

N channel

$V_{DS}(V)=30V$

$I_D=2.7A$

$R_{DS(ON)}@10V<80m$ (TYP. 66 m)

$R_{DS(ON)}@4.5V<130m$ (TYP. 95 m)

HF Product.

P-channel

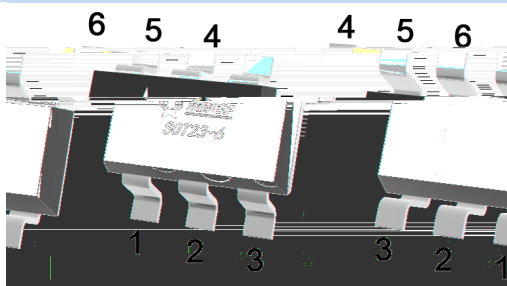
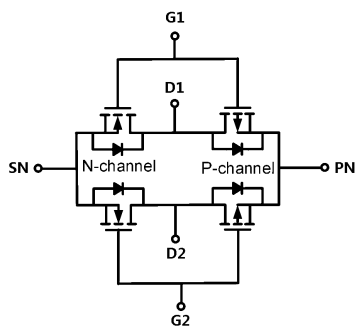
$V_{DS}(V)=-30V$

$I_D=-2.6A$

$R_{DS(ON)}@-10V<95m$ (TYP. 75 m)

$R_{DS(ON)}@-4.5V<150m$ (TYP. 88 m)

PWM applications, Load switch.

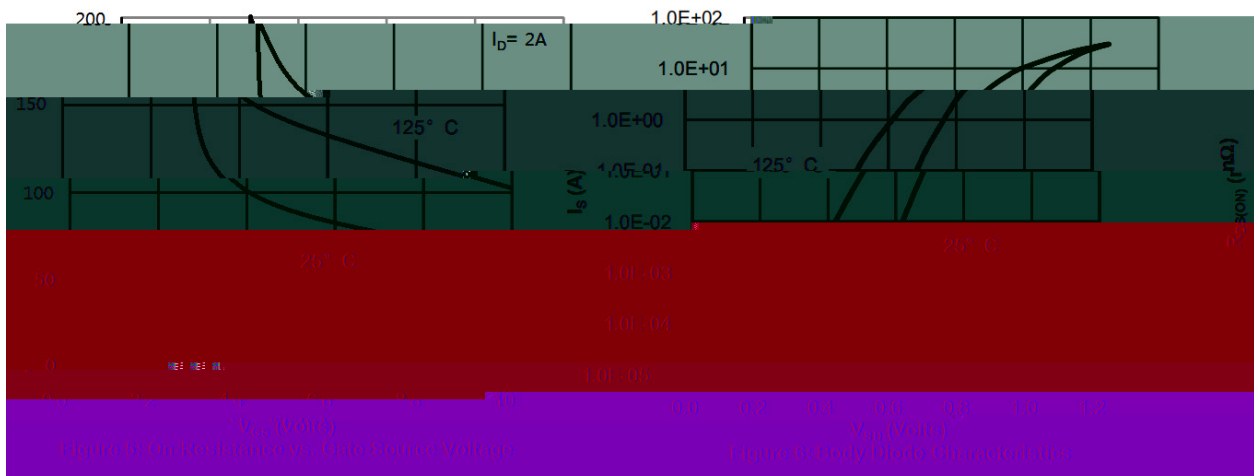
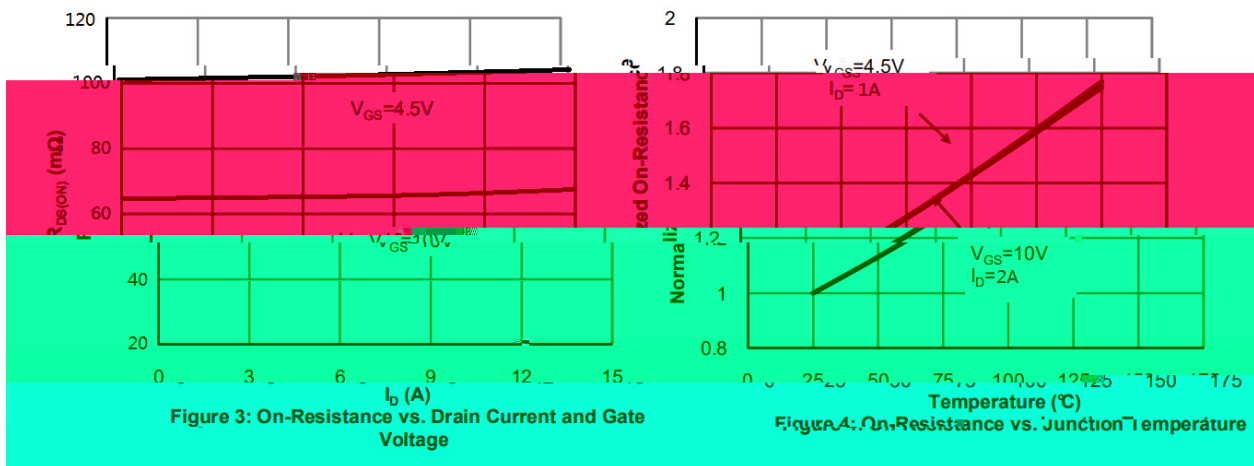
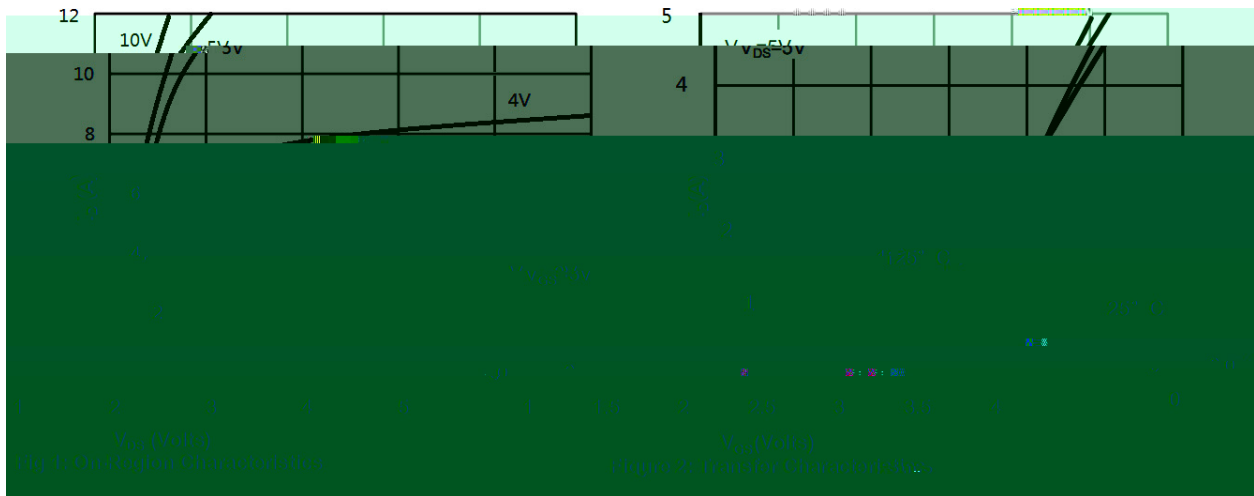


PIN1	G1	PIN 2	SN	PIN 3	G2
PIN 4	D2	PIN 5	SP	PIN 6	D1

See Marking Instructions.

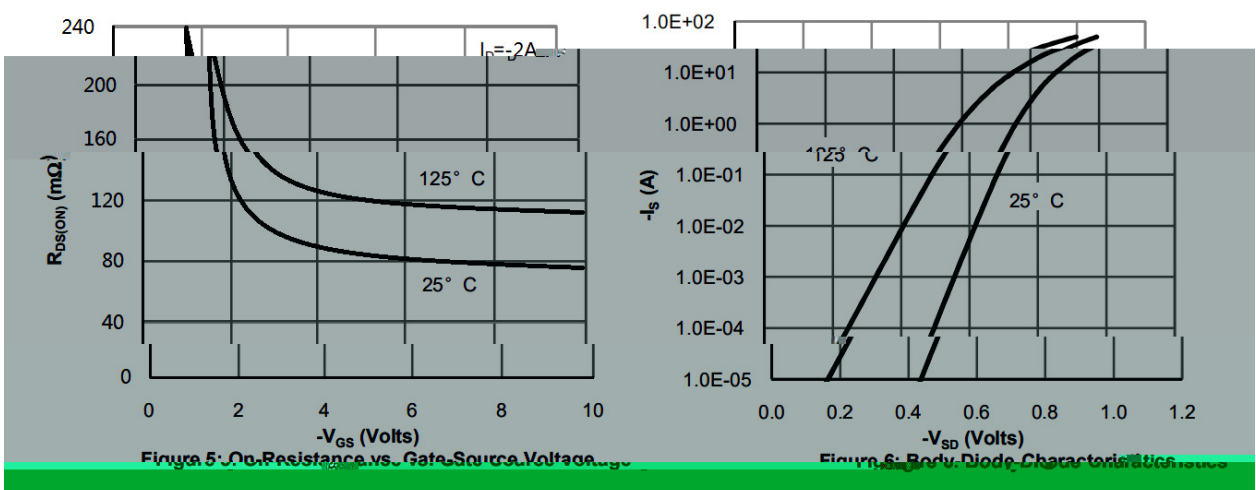
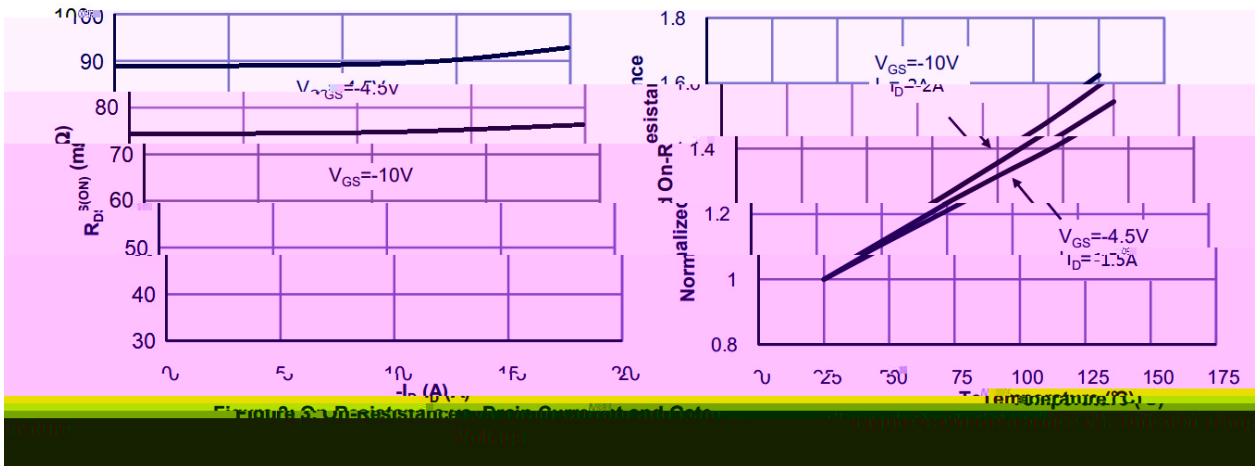
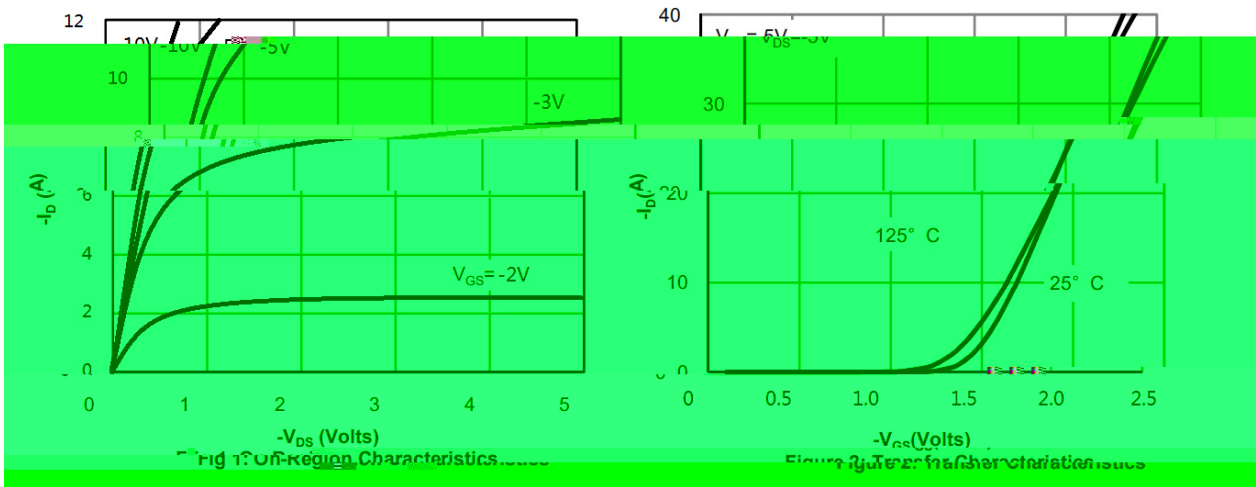
Parameter	Symbol	Rating		Unit
		N-channe	P-channell	
Drain-Source Voltage	V_{DSS}	30	-30	V
Gate-Source Voltage	V_{GSS}	± 20		V
Continuous Drain Current	I_D	2.7	-2.6	A
Pulsed Drain Current	I_{DM}	7	-7	A
Power Dissipation	P_D	1		W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150		
Maximum Junction-to-Ambient	$R_{\theta JA}$	125		

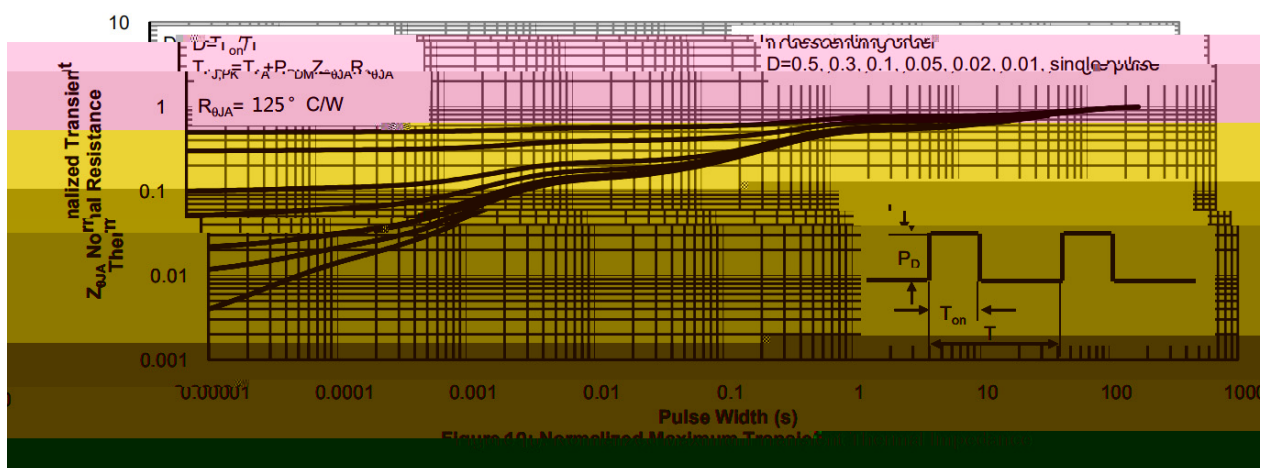
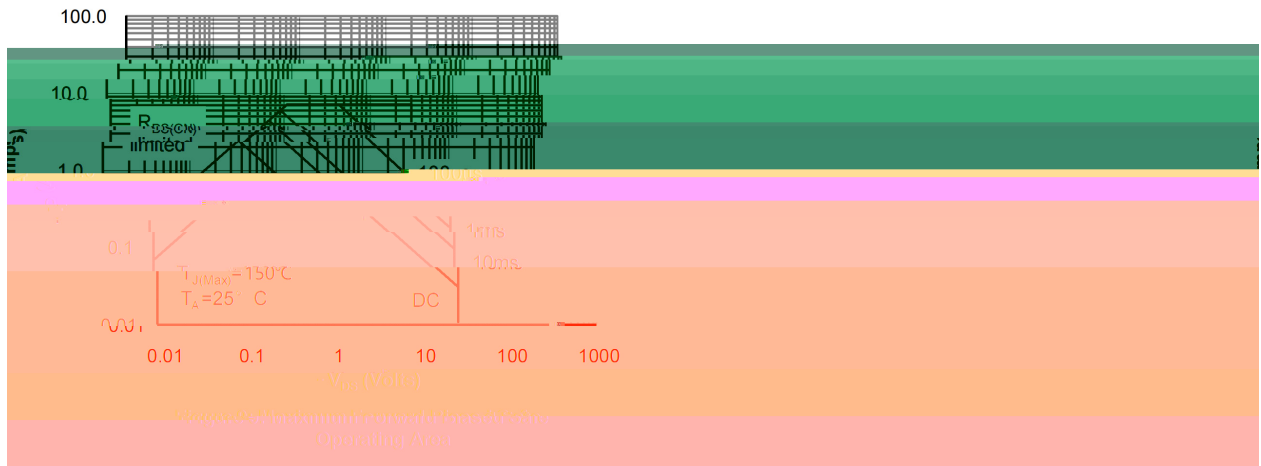
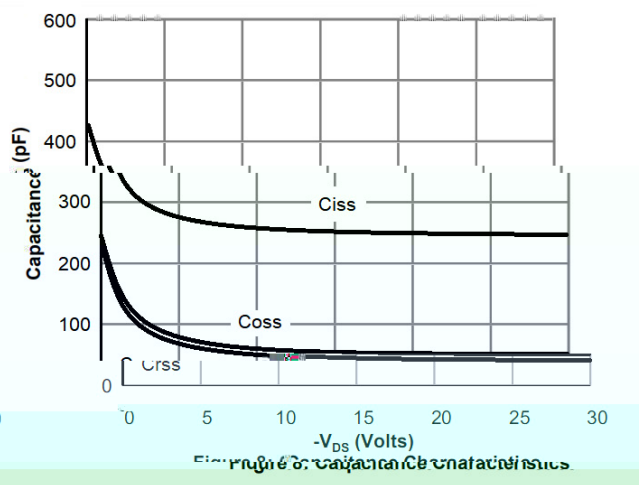
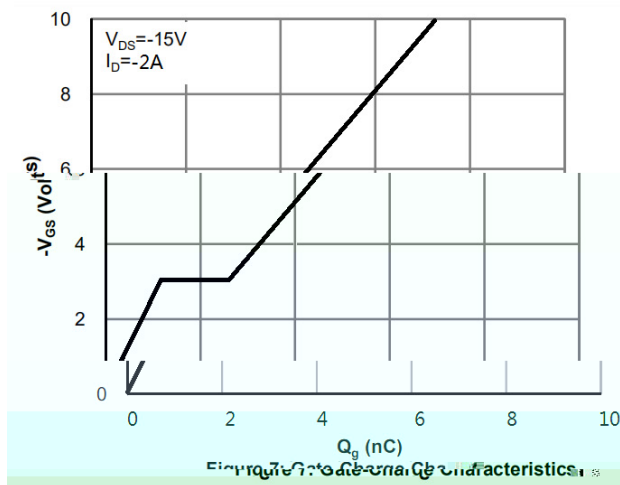
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0$ $I_D=250\mu A$	30	31.5		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0$ $V_{DS}=24V$			1.0	μA
Gate-Body Leakage.	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 100	nA
Static Drain-Source On-Resistance	$R_{DS(on)1}$	$V_{GS}=10V$ $I_D=2.0A$		66	80	m Ω
	$R_{DS(on)2}$	$V_{GS}=4.5V$ $I_D=1.0A$		95	130	m Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_D=1.0A$			1.2	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.45	2.0	V
Input Capacitance	C_{iss}	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0MHz$		200		pF
Output Capacitance	C_{oss}			30		pF
Reverse Transfer Capacitance	C_{rss}			20		pF
Total Gate Charge	Q_g	$V_{GS}=10V$, $I_D=2A$ $V_{DS}=15V$		5		nC
Gate Source Charge	Q_{gs}			0.8		
Gate Drain Charge	Q_{gd}			1.7		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=15V$ $R_{GEN}=6\Omega$ $I_D=1A$		4		ns
Turn-On Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			9		
Turn-Off Fall Time	t_f			2.2		

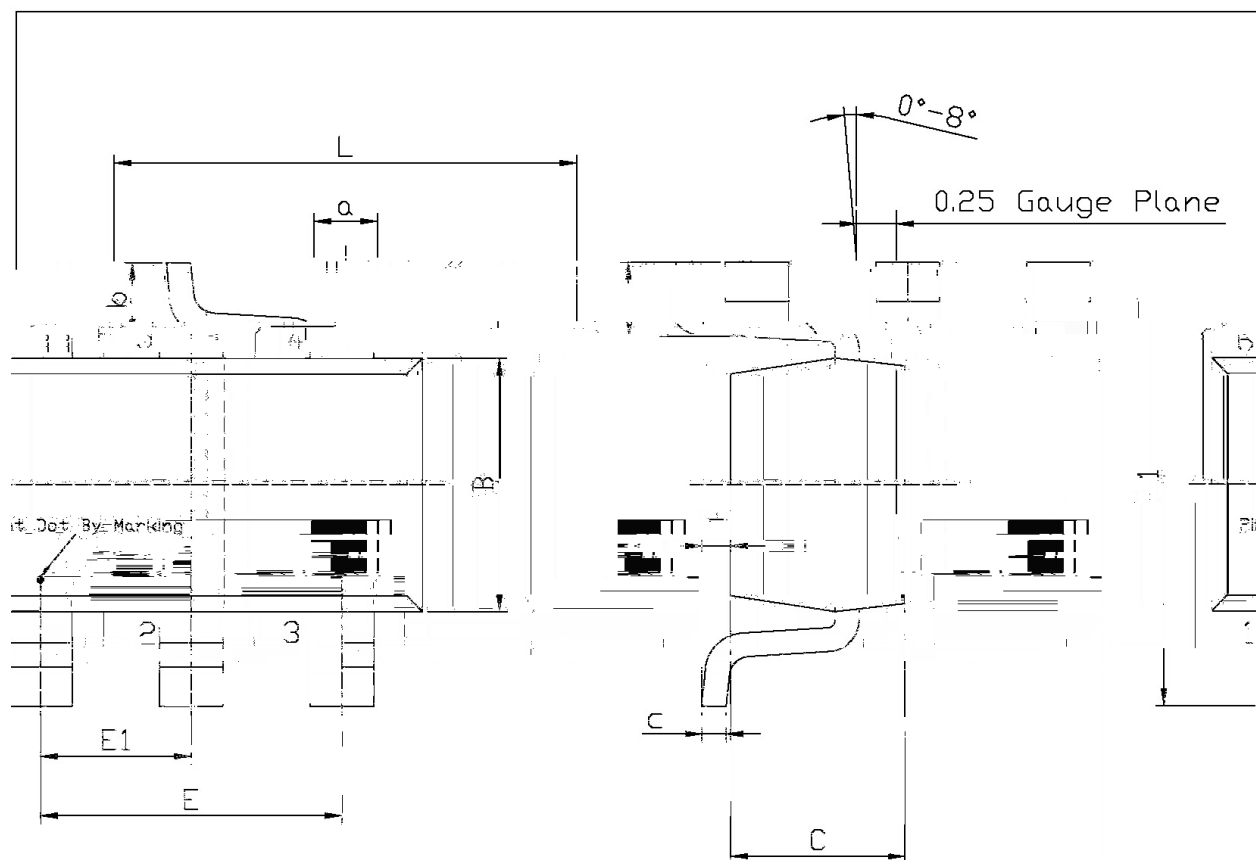




Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V$ $I_D=-250\mu A$	-30	-31.5		V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250\mu A$	-0.5	-0.85	-2.0	V
Static Drain–Source On–Resistance	$R_{DS(on)}$	$V_{GS}=-10V$ $I_D=-2A$		75	95	$m\Omega$
	$R_{DS(on)}$	$V_{GS}=-4.5V$ $I_D=-1.5A$		88	150	$m\Omega$
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V$ $V_{GS}=0V$			-1	μA
Gate–Body Leakage	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	μA
Drain–Source Diode Forward Voltage	V_{SD}	$I_S=-1.0A$ $V_{GS}=0V$			-1.2	V
Input Capacitance	C_{iss}	$V_{DS}=-15V$, $f=1MHz$ $V_{GS}=0V$		250		pF
Output Capacitance	C_{oss}			50		
Reverse Transfer Capacitance	C_{rss}			40		
Total Gate Charge	Q_g	$V_{DS}=-15V$ $V_{GS}=-10V$ $I_D=-2A$		7.2		nC
Gate-to-Source Charge	Q_{gs}			1.1		
Gate-to-Drain Charge	Q_{gd}			1.6		
Turn–On Delay Time	$t_{d(on)}$	$V_{DS}=-15V$ $V_{GS}=-10V$ $R_{GEN}=6\Omega$ $I_D=2A$		7.5		ns
Turn–On Rise Time	t_r			11.8		
Turn–Off Delay Time	$t_{d(off)}$			17		
Turn–Off Fall Time	t_f			6		



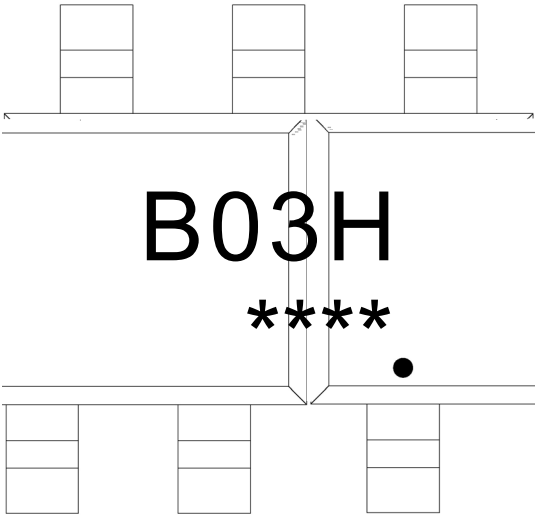




Unit: mm

Dimensions In Millimeters			Dimensions In Millimeters		
Symbol	Min	Max	Symbol	Min	Max
L	2.82	3.32	E1	0.85	1.05
B	1.50	1.70	a	0.35	0.50
C	0.90	1.30	c	0.10	0.20
L1	2.60	3.00	b	0.35	0.55
E	1.80	2.00	F	0	0.15

SOT23-6

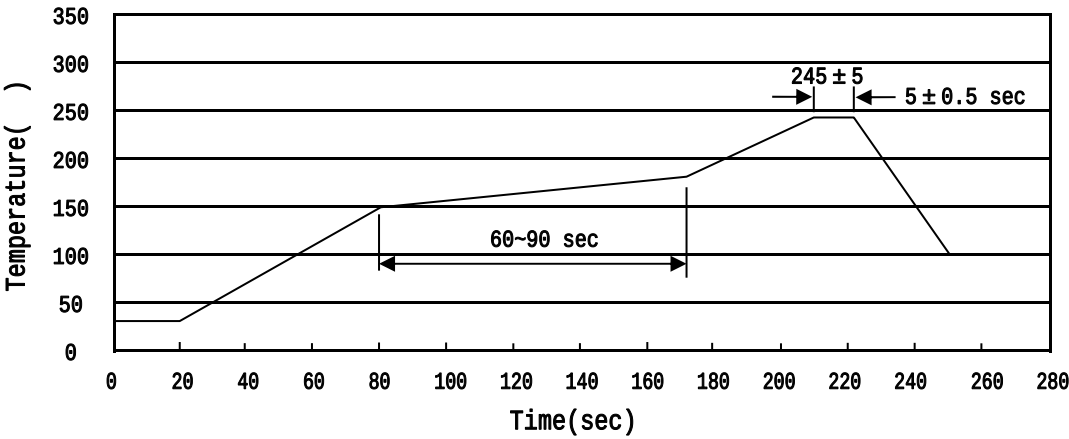


B03:

****.

Note:

B03	Product Type Code
H	Company Code
****.	Lot No.Code,code change with Lot No



Note:

- 1

150 180

60 90sec;

1.Preheating:150~180 , Time:60~90sec.
- 2

245 5

5 0.5sec;

2.Peak Temp.:245 5 , Duration:5 0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260 5

10 1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱
SOT23-5/6	3,000	10	30,000	4	120,000	7 ×8	210×205×205	445×435×230